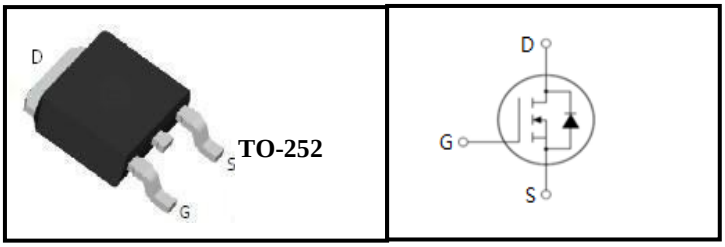
FEATURES

- BV_{DSS}=60V, I_D=50A
- $R_{DS(on)}$: 17mΩ(Max)@V_{GS}=10V
- $R_{DS(on)}$: 20mΩ(Max)@V_{GS}=4.5V
- 100% avalanche tested
- RoHS compliant



APPLICATIONS

- Load Switch
- Power Management
- Motor Drive Application

RoHS

Device Marking and Package Information

Ordering code	Package	Marking
MPTD50N60N	TO-252	MPTD50N60N

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage (V_{GS} = 0V)		V_{DSS}	60	V
Continuous Drain Current		I_D	50	A
Pulsed Drain Current	(note1)	I_{DM}	200	A
Gate-Source Voltage		V_{GSS}	±20	V
Single Pulse Avalanche Energy	(note2)	E_{AS}	64	mJ
Power Dissipation (T_C = 25ºC)		P_D	75	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+175	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2.0	K/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	60	

Specifications T_J = 25ºC, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Value**			**Unit**
			Min.	**Typ.**	**Max.**	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60V, V_{GS} = 0V, T_J = 25ºC	--	--	1.0	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 0.25mA	1.0	1.6	2.5	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	V_{GS} = 10V, I_D = 30A	--	11.5	17	mΩ
		V_{GS} = 4.5V, I_D = 20A	--	13.0	20	mΩ
Gate Resistance	R_G	f = 1.0MHz, open drain	--	2.0	--	Ω
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz	--	2900	--	pF
Output Capacitance	C_{oss}		--	140	--	
Reverse Transfer Capacitance	C_{rss}		--	120	--	
Total Gate Charge	Q_g	V_{DS} = 30V, I_D = 30A, V_{GS} = 10V	--	50	--	nC
Gate-Source Charge	Q_{gs}		--	8	--	
Gate-Drain Charge	Q_{gd}		--	9	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 30V, R_L = 6Ω V_{GS} = 10V, R_G = 1.8Ω	--	10	--	ns
Turn-on Rise Time	t_r		--	6	--	
Turn-off Delay Time	$t_{d(off)}$		--	25	--	
Turn-off Fall Time	t_f		--	7	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	50	A
Pulsed Diode Forward Current	I_{SM}		--	--	200	
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 30A, V_{GS} = 0V	--	--	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 30V, I_F = 30A, di_F/dt = 100A/μs	--	30	--	ns
Reverse Recovery Charge	Q_{rr}		--	40	--	nC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 0.5mH, V_{DD} = 30V, R_G = 25Ω, Starting T_J = 25°C
3. Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 0.5%

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

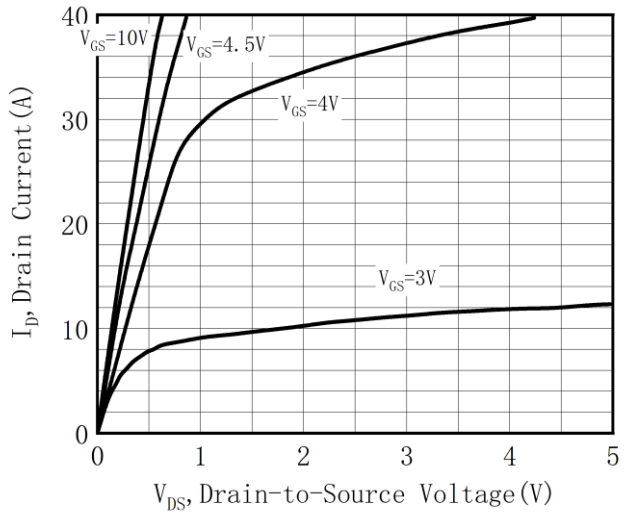


Figure 2. Transfer Characteristics

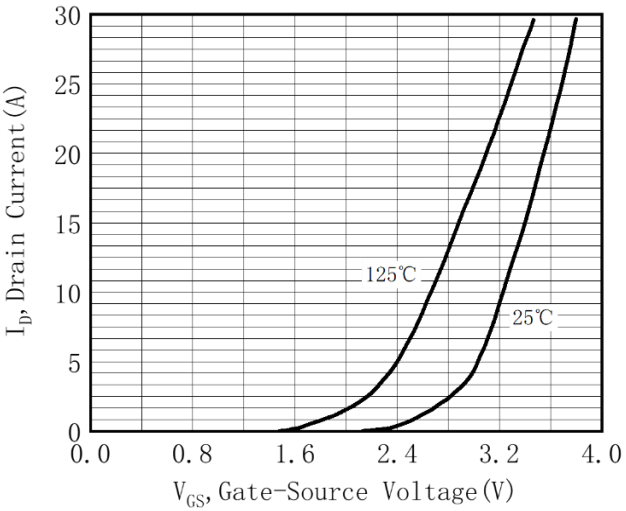


Figure 3. On-Resistance vs Drain Current

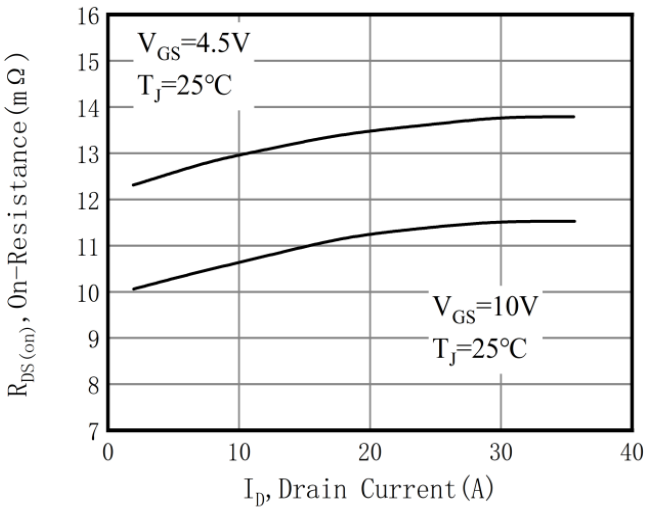


Figure 4. Capacitance

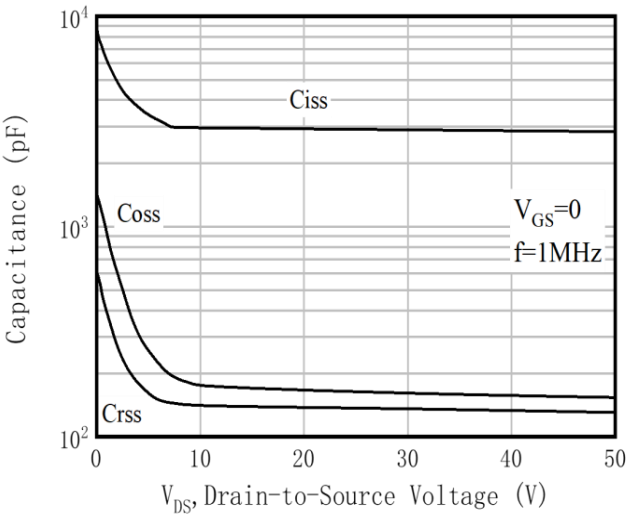


Figure 5. Gate Charge

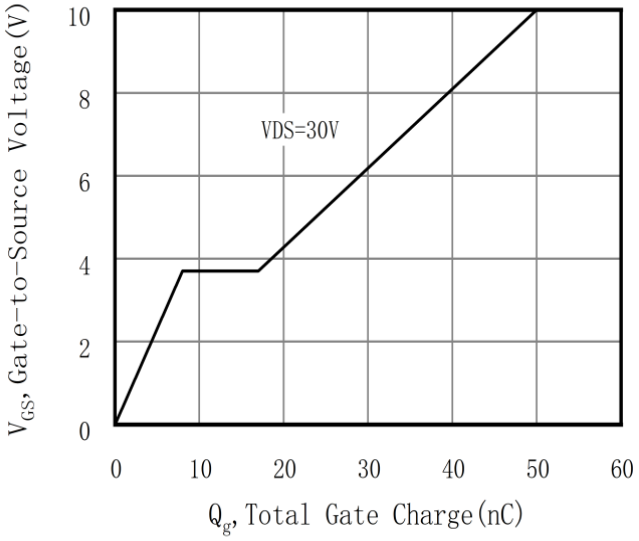
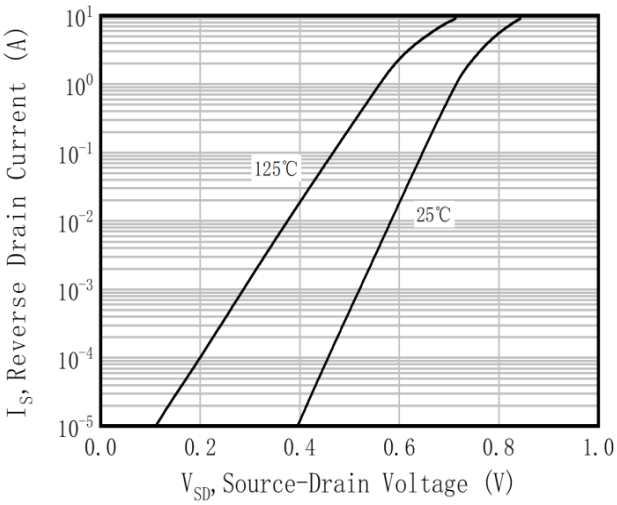


Figure 6. Body Diode Forward



Typical Characteristics T_J = 25℃, unless otherwise noted

Figure 7. On-Resistance vs Junction Temperature

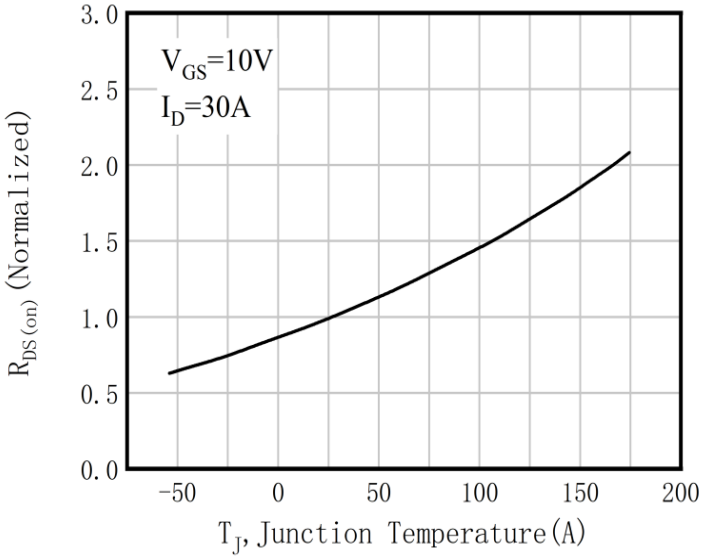


Figure 8. Threshold Voltage vs Junction Temperature

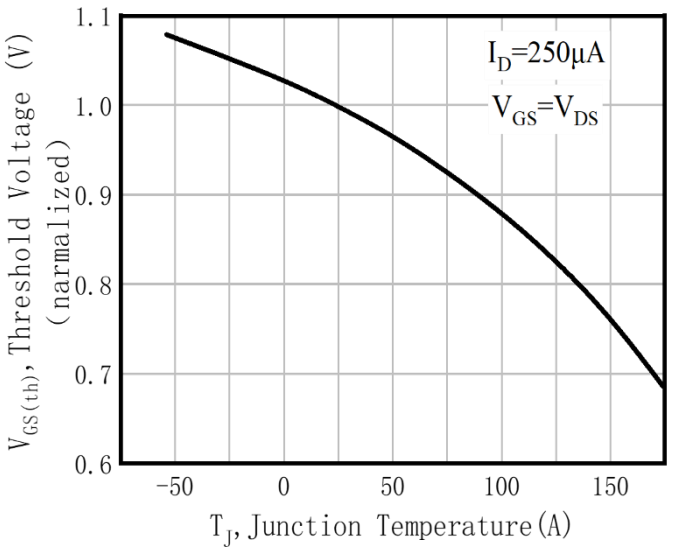


Figure 9. Transient thermal Impedance

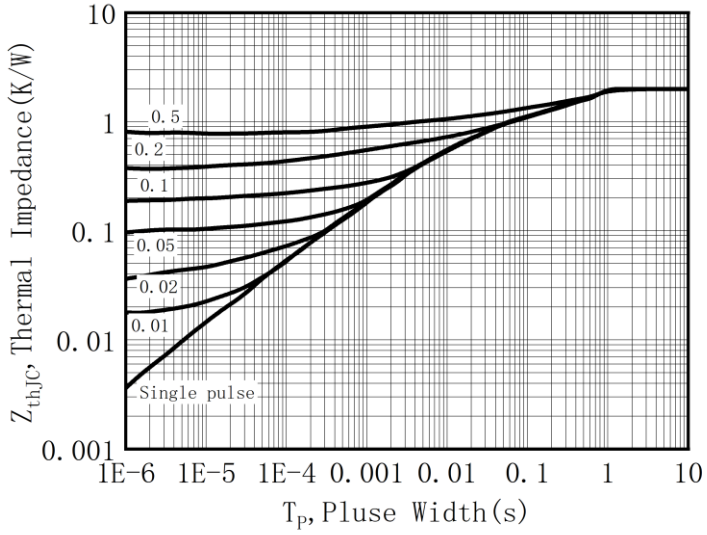


Figure 10. Safe Operating Area

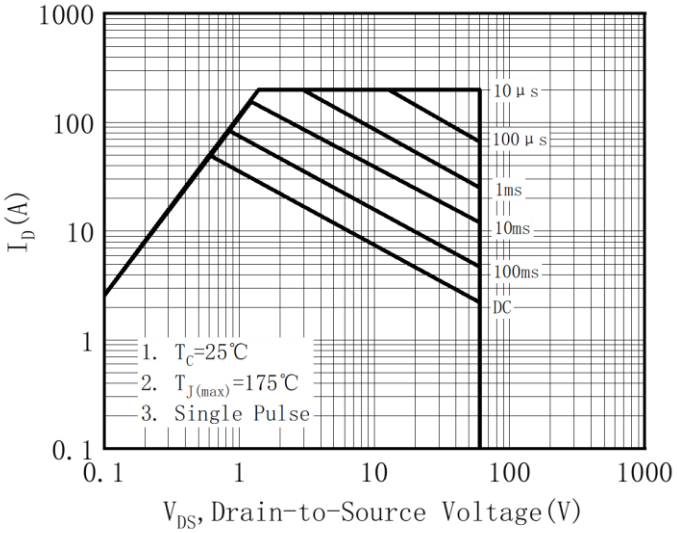


Figure A：Gate Charge Test Circuit and Waveform

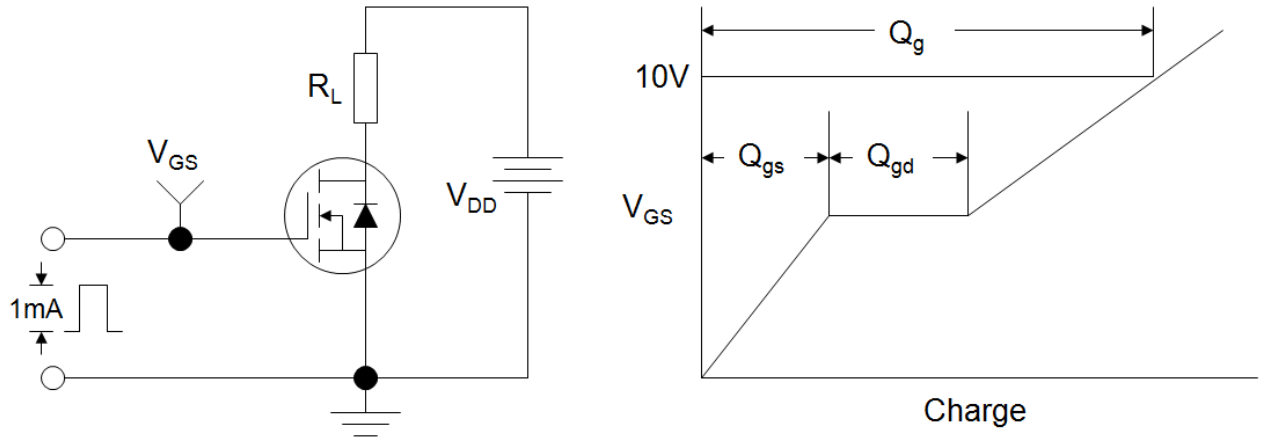


Figure B：Resistive Switching Test Circuit and Waveform

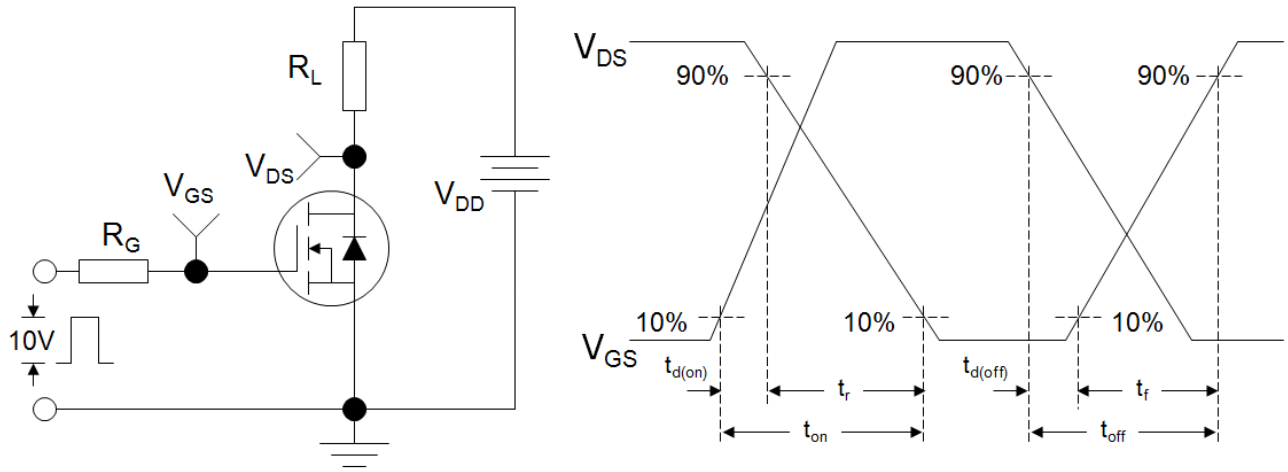
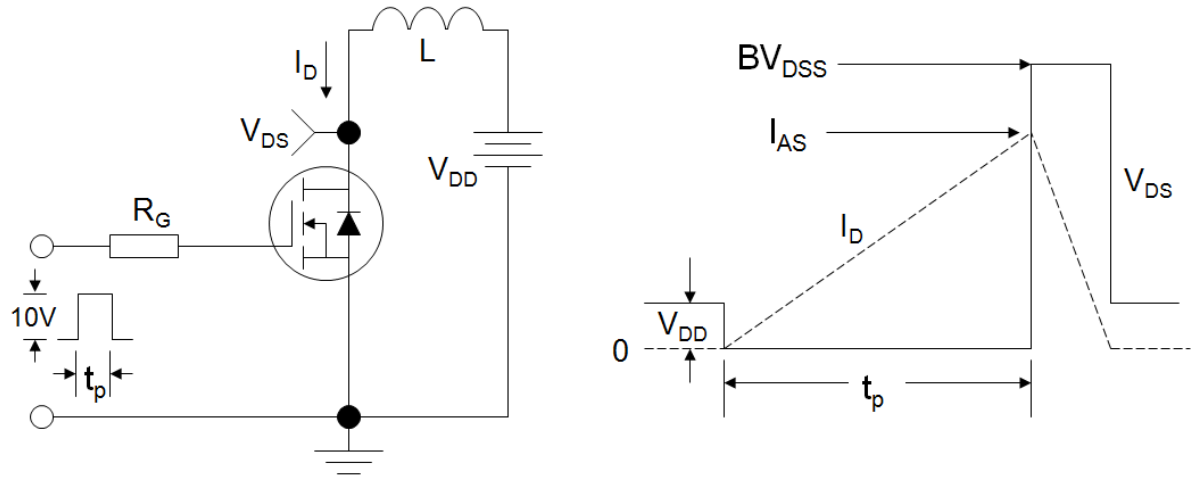
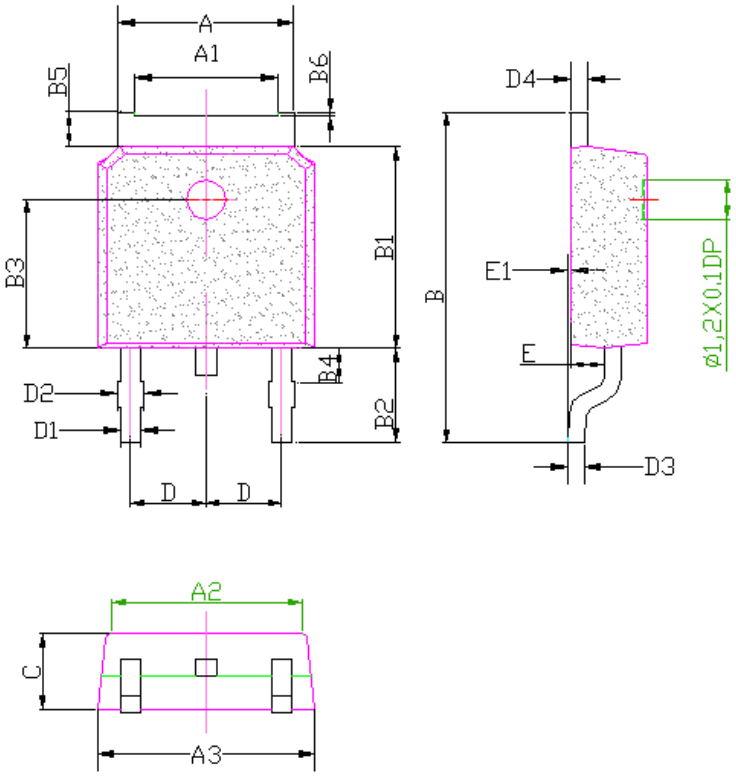


Figure C：Unclamped Inductive Switching Test Circuit and Waveform



TO-252 Package Information



DIM	MILLIMETERS
A	5.33±0.2
A1	4.33±0.2
A2	5.80±0.1
A3	6.6±0.2
B	10±0.5
B1	6.1±0.3
B2	2.85±0.5
B3	4.5±0.15
B4	1.0±0.1
B5	1.05±0.1
B6	0.1±0.05
C	2.3±0.15
D	2.286±0.05
D1	0.60±0.1
D2	0.72±0.12
D3	0.5±0.08
D4	0.5±0.08
E	1.01±0.15
E1	0.1±0.05
DIA	⊙1.2(deep 0.1)

Unit :mm